

Substitute for Form 1449 A & B/PTO <u>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</u> <i>(use as many sheets as necessary)</i>			<i>Complete if Known</i>		
			Application Number	10/519,084	
			Confirmation Number	7332	
			Filing Date	December 23, 2004	
			First Named Inventor	Heiji WATANABE	
			Art Unit	2822	
Examiner Name	Tsz K. CHIU				
Attorney Docket Number	Q85504				
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
/TC/		US 6,380,104	B1	04-30-2002	Yu
		US			
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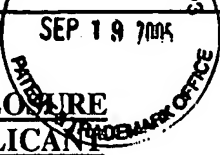
FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			

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/TC/		H.-J. Cho, et al.: "Novel Nitrogen Profile Engineering for Improved TaN/HfO ₂ /Si MOSFET Performance"; IEDM, Technical Digest 2001, pages 655-658	

Examiner Signature	/Tsz Chiu/ (06/11/2007)	Date Considered	06/11/2007
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¹ Applicant's unique citation designation number (optional). ² See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or follow the hyperlink from the title of the document to the intranet. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to indicate here if English language Translation is attached.

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		Examiner Name		Not Yet Assigned	
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/TC/		JP	2002-60944	A	02-28-2002	Internatl Business Mach Corp	
/TC/		JP	10-242461	A	09-11-1998	Sony Corp	
/TC/		JP	2002-164343	A	06-07-2002	Agere Systems Guardian Corp	
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/TC/		JP	2001-358225	A	12-26-2001	Agere Systems Guardian Corp	
/TC/		JP	2001-85427	A	03-30-2001	NEC Corp	
/TC/		JP	2001-257344	A	09-21-2001	Toshiba Corp	
/TC/		JP	2001-332547	A	11-30-2001	Toshiba Corp	
/TC/		JP	11-261067	A	09-24-1999	Texas Instr Inc	

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Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
/TC/		H.-J. Cho et al.; "Novel Nitrogen Profile Engineering for Improved TaN/HfO ₂ /Si MOSFET Performance"; International Electron Devices Meeting; Technical Digest 2001; pages 655-658.	
/TC/		Hag-Ju Cho, et al.; "Structural and Electrical Properties of HfO ₂ With Top Nitrogen Incorporated Layer"; IEEE Electron Device Letters; Vol. 23 No. 5, May 2002; pages 249-251.	
/TC/		M. Koyama, et al.; "Thermally Stable Ultra-Thin Nitrogen Incorporated ZrO ₂ Gate Dielectric Prepared by Low Temperature Oxidation of ZrN"; Tech. Dig. IEDM 2001; pages 459-462.	

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Application Number	Unknown 10/519084
Confirmation Number	Not yet assigned
Filing Date	December 23, 2004
First Named Inventor	Heiji WATANABE
Art Unit	Not yet assigned
Examiner Name	Not yet assigned
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TC/		JP	2002-060944	A	02-28-2002	IBM Corp.	ABS

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TC/		M. Koyama et al., "Thermally Stable Ultra-Thin Nitrogen Incorporated ZrO ₂ Gate Dielectric Prepared by Low Temperature Oxidation of ZrN", Technical Digest, IEDM, December 2-5, 2001, pages 459-462.	
TC/		Hag-Ju Cho et al., Novel Nitrogen Profile Engineering for Improved TaN/HfO ₂ /Si MOSFET Performance, IEDM, Technical Digest 2001, pages 655-658.	
TC/		Hag-Ju Cho et al., Structural and Electrical Properties of HfO ₂ with Top Nitrogen Incorporated Layer, IEEE Electron Device Letters, Vol. 23, No. 5, May 2002, pages 249-251.	

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